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1.2 V, 40 – 900 MHz BROADBAND AMPLIFIER WITH THE TP3400 TRANSISTOR

INTRODUCTION

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APPLICATION NOTE

This application note describes a single stage broadband amplifier incorporating the TP3400 transistor. The amplifier will deliver 1.2 V output signal from 40 to 900 MHz at an intermodulation level* of – 60 dB or less. The gain is 9.5 dB \pm 0.5 dB. Although the amplifier has been designed for MATV use, its simplicity and versatility makes it suitable for use in many other applications. The circuit construction is straight forward and only standard components have been used.

TP3400

niconductor

eescale

The TP3400 is a NPN gold metallized transistor with a transition frequency of more than 3 GHz. The transistor is housed in a SOE 200 package.

The gold metallization process used on the manufacture of this transistor is etchless, providing exact finger definition with submicron resolution and avoids the finger scalloping characteristic of all etching processes, which eliminates therefore current crowding where metal fingers are necked down. Moreover this gold process improves on all the benefits of gold over aluminum regarding electromigration.

The TP3400 also incorporates diffused ballast resistors. High resistance ballast resistors are diffused directly into the silicon avoiding therefore all the reliability problem associated with conventional thin film, metal ballast resistors. In addition the P-N diode of the ballast resistor is diffused to avalanche at a lower voltage than the transistor, thus protecting effectively the transistor against VSWR or transient damage. A diagram illustrating the above mentioned technological characteristic is given in Figure 1.

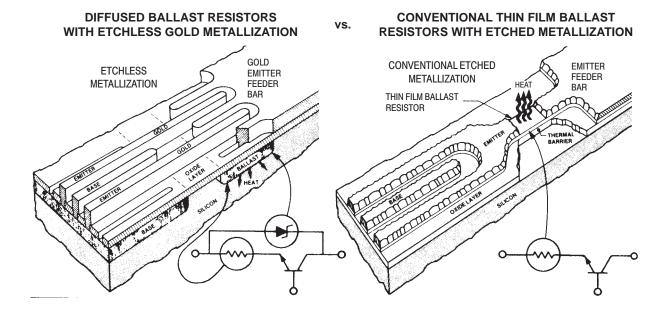


Figure 1. Types of Ballast Resistors

* Intermodulation measured with a test procedure in accordance with DIN 45004/B.





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AMPLIFIER DESIGN

a) Calculations

The amplifier configuration chosen is given in Figure 2. A combination of series and shunt feedback compensates the frequency gain slope of the transistor. Transmission line inductors are used on the shunt feedback network. The resistor in series with the base will improve the input VSWR at the cost of some gain, but this gain decrease is partially compensated by the fact that less series feed-back is necessary in this way.

The calculation and optimization of the circuit was carried out with the aid of a computer using the COMPACT program. The program, the optimization data and the final expected results are given in Table 1. The expected gain is 9.5 dB plus/minus 0.5 dB, the amplifier is unconditionally stable over the required frequency range and input and output impedance matchings could be considered correct.

b) Amplifier assembly

Final amplifier is shown in Figure 3. The component values are given in Table 2. The amplifier was built on standard Epoxy glass double clad printed circuit board and all the components are commonly used types. The resistors are carbon-composition type. Care was taken with all ground returns, made by wrapping copper foil between both planes. Plated trough holes may also be used. PC board and component layouts are given in Figures 4 and 5 respectively.

RESULTS

Several TP3400 transistors, covering all the accepted production spread, were used and no significant differences in the amplifier performance were recorded.

Input and output matching are given in Figures 6 and 7. Gain versus frequency is given in Figure 8. It is similar to that calculated.

Figure 9 shows its behavior as an MATV amplifier, measured according to the DIN 45004B test procedure. The -60 dB IMD level is attained at 1.2 volt, 75 output.

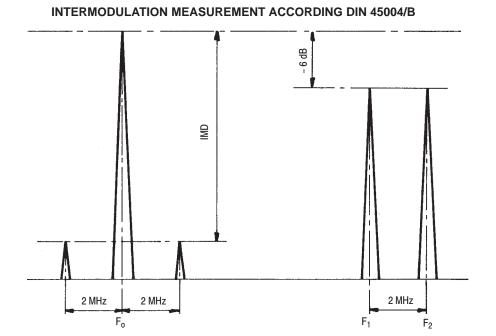




Table 1. Compact Program

										- J
MET CAP TRL	AA AA BB	PA SE	6	2.078	- 19.9	61.	000			
RES TRL CAP TWO	CC DD EE HH	SE PA	6 - 2	2.44 5.00 2.101 50.00	- 18.3	51.	000			
CAS RES SER	EE II EE	PA II		6.759						
CAP SRL TRL CAX	JJ Kł LL JJ	. SE	3	8989 35.00 35.00	1000 - 10.1		000		(ightarrow CIRCUIT DEFINITION
CAS RES TRL CAS	EE MN NN MN	A SE		204.7 65.00	- 7.22	91.	000			
PAR TRL CAP CAX	EE FF GG AA	SE PA	6 . –	65.00 9557	- 14.6	01.	000			
PRI END 100	AA 200	SI 300	5 400	50.00	600	700	800	900	J	
END	200	300	400	500	000	700	800	900	ſ	FREQUENCY (MHz)
.61 .73 .75 .75 .75 .78 .77 .77 END	226 203 192 185 179 174 167 163	17.8 12.9 9.23 6.92 5.15 4.68 3.34 3.16	126 103 93 84 79 72 61 56	.0200 .0282 .0299 .0335 .0335 .0355 .0447 .0473	35 33 33 33 38 42 44 44	.53 .32 .27 .27 .27 .24 .27 .24	320 305 297 295 300 300 285 290			POLAR S–PARAMETERS FOR TWO HH (TP3400)
.5 10 END	10	1	10						}	OPTIMIZATION DATA

POLAR S-PARAMETERS IN 50 OHM SYSTEM

FREQ.	S11		S21		S12		S22		S21	K
	(MAGN	ANGL)	(MAGN	ANGL)	(MAGN	ANGL)	(MAGN	ANGL)	dB	FACT
100	0.09	- 132	2.99	157.1	0.139	- 10.7	0.16	149	9.52	1.38
200	0.11	- 140	3.14	135.2	0.139	- 21.5	0.16	141	9.94	1.33
300	0.13	- 152	3.13	113.4	0.136	- 32.7	0.11	128	9.91	1.36
400	0.15	- 166	3.14	89.7	0.133	- 43.6	0.03	86	9.94	1.38
500	0.15	166	2.94	64.2	0.128	- 53.5	0.07	- 52	9.37	1.49
600	0.15	140	3.15	43.9	0.126	- 63.6	0.10	- 68	9.96	1.42
700	0 15	99	3.18	20.0	0.127	- 72.3	0.16	- 99	10.05	1.37
800	0 20	51	2.95	- 6.8	0.128	- 80.8	0.25	- 120	9.38	1.34
900	0.26	18	3.06	- 29.3	0.128	- 93.0	0.25	- 125	9.78	1.22



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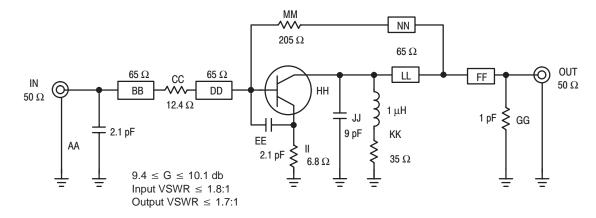


Figure 2. TP 3400 Amplifier 40 - 900 MHz

Table 2. List of Components

	•
$\begin{array}{c} C_1 \\ C_2 \\ C_3 \\ C_4 \\ C_5, C_7 \\ C_6, C_8 \\ C_9 \\ C_{10} \\ C_{11} \end{array}$	 = capacitor ceramic 2.8 pF 632 RTC = capacitor chip 10 nF Eurofarad = capacitor chip 8.2 pF Vitramon = capacitor chip 2.2 pF Vitramon = capacitor chip 1 nF Eurofarad = capacitor chip 10 nF Eurofarad = capacitor chip 22 pF Vitramon = capacitor chip 10 nF Eurofarad = capacitor chip 10 nF Eurofarad = capacitor chip 10 nF Eurofarad
L ₁ L ₂ L ₃ L ₄ L ₅ F ₁	 = 8 turns 5/10 mm Cu ID 2.5 mm = printed 5 nH = printed stripline 75 ohms 11.5 mm = printed stripline 75 ohms 11 mm = printed stripline 75 ohms 25 mm = ferrite bead 1200082 TRW
R ₁ R ₂ R ₃ , R ₄ R ₅ R ₆ R ₇	 = resistor 12 ohms 1/4 W carbon composition = resistor 4.7 ohms 1/4 W carbon composition = resistor 10 ohms 1/4 W carbon composition = resistor 8.2 kohms 1/4 W carbon composition = resistor 240 ohms 1/4 W carbon composition = resistor 12 ohms 1/2 W carbon composition

T = transistor TP3400

Board Material

Epoxy glass (G 10) 1/16 inch ϵ_R = 4.2

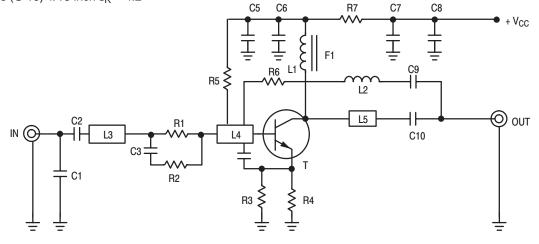


Figure 3. Circuit Schematic

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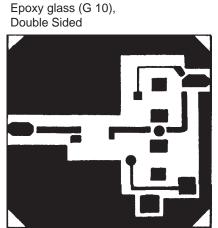


Figure 4. PC Board Layout (Not to Scale)

INPUT

+++ FOIL WRAP OR PLATE AROUND PLANE

Figure 5. Component Layout

Chart Not Available Electronically

Inch

1

3 C m

OUTPUT

+ Vcc (20.5 V)

Ż

C9

1

Figure 6. S₁₁ versus Frequency





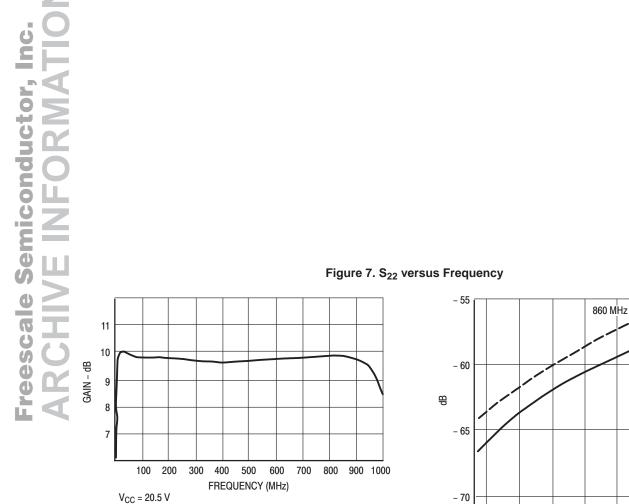




Figure 8. Gain versus Frequency

RF Application Reports

500 MHz

V/75 Ω

1.5

I_C = 125 mA

- 70

1

V_{CE} = 18 V

Figure 9. IMD (Din 45004 B) versus Output Voltage

V_{CE} = 18 V I_C = 125 mA



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